Form PTO-1449 (REV. 8-83)	US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 117576	APPLICATION NO. 10/690,025
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		FILING DATE October 22, 2003	

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EXAMINER G. MUNSON	DATE CONSIDERED 18 FEBRUARY 2005

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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